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Docket No.: Z0200.0001/P001

Application No.: Not Yet Assigned

1. (Original) A process for the selective removal of sulphur compounds from synthesis gas containing at least 5% carbon monoxide, at least 5% hydrogen and at least 0.5% carbon dioxide and optionally containing water in a concentration up to saturation at a pressure of at least 15 bar comprising contacting the synthesis gas at a maximum contact

AMENDMENTS TO THE CLAIMS

temperature of 100°C with an absorbent comprising Cu/ZnO compounds and activated

with a reducing gas.

2. (Original) Process of claim 1, wherein the sulphur compounds comprise H<sub>2</sub>S

and COS.

3. (Currently amended) Process according to claim 1 any one of the preceding

<del>claims</del>, wherein the synthesis gas contains H<sub>2</sub>S in an amount effective for suppression of

metal dusting of metals in contact with the synthesis gas within a temperature range

between 300°C to Boudouard temperature of the synthesis gas.

2